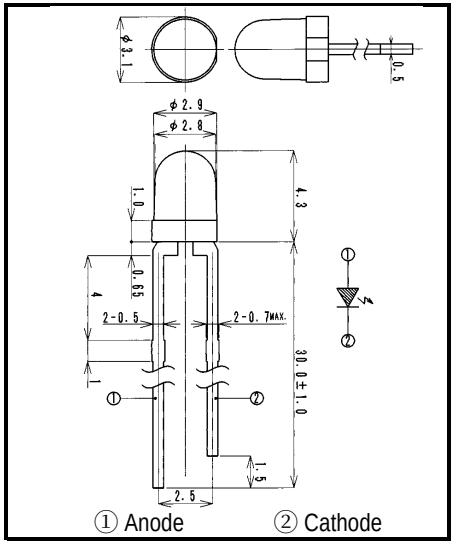
LSF811C1 *Infrared Emitting Diode*





Dimensions (Unit:mm)

FEATURES
- High-output Power
- Compact
- High Reliability

APPLICATIONS
- Optical Switches
- Optical Sensors
- Medical Application

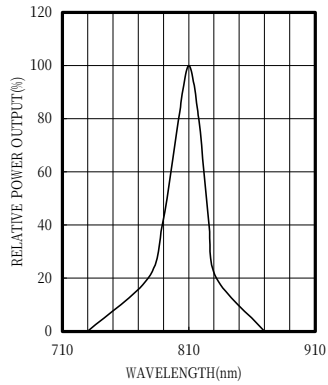
1. ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

I T E M	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	60	mA
Forward Current (Pulse)*1	IFP	0.5	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	120	mW
Operating Temp.	Topr	-20 TO 85	℃
Storage Temp.	Tstg	-30 TO 100	℃
Junction Temp.	Tj	100	℃
Lead Soldering Temp.*2	Tls	260	℃

*1:Tw=10uS,T=10mS

*2:Time 5 Sec max,Position:Up to 3mm from the body

SPECTRAL OUTPUT



To purchase this part contact
Marktech Optoelectronics at
800.984.5337

Marktech Optoelectronics
www.marktechopto.com

Pb lead-free RoHS

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2.ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25℃)

I T E M	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=20mA		6.5		mW
Forward Voltage	VF	IF=20mA		1.4	1.9	V
Reverse Current	IR	VR=5V			100	μA
Peak Wavelength	λp	IF=20mA		810		nm
Spectral Line Half Width	Δλ	IF=20mA		30		nm
Half Intensity Beam Angle	θ	IF=20mA		±25		deg.
Rise Time	Tr	IFP=50mA		—		nS
Fall Time	Tf	IFP=50mA		—		nS
Junction Capacitance	Cj	1MHz ,V=0V		60		pF
Temp. Coefficient of PO	P/T	IF=10mA		-0.6		%/℃
Temp. Coefficient of VF	V/T	IF=10mA		-2.0		mV/℃

